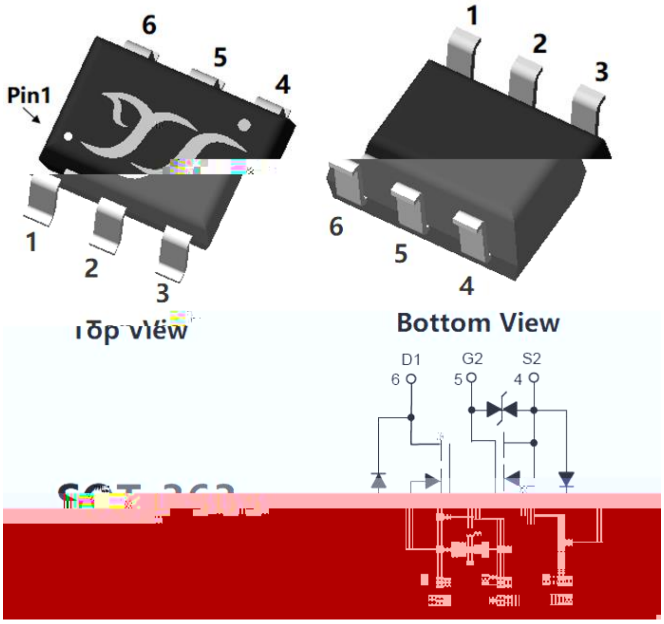
N-Channel Enhancement Mode Field Effect Transistor



Product Summary

ǒ V_{DS}	20 V
ǒ I_D	0.8 A
ǒ $R_{DS(ON)}$(at V_{GS}=4.5V)	300 mohm
ǒ $R_{DS(ON)}$(at V_{GS}=2.5V)	400 mohm
ǒ $R_{DS(ON)}$(at V_{GS}=1.8V)	700 mohm

ǒ ESD Protected Up to 2.0KV (HBM)

General Description

ǒ Trench Power LV MOSFET technology
ǒ High Power and current handing capability
ǒ Moisture Sensitivity Level 1
ǒ Epoxy Meets UL 94 V-0 Flammability Rating
ǒ Halogen Free

Applications

ǒ PWM application
ǒ Load switch

ƴ **Absolute Maximum Ratings** (T_A=25 unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	20	V
Gate-source Voltage		V_{GS}	12	V
Drain Current	T_A=25 @ Steady State	I_D	0.8	A
	T_A=70 @ Steady State		0.6	
Pulsed Drain Current ^{A}		I_{DM}	3.3	A
Total Power Dissipation @ T_A=25		P_D	0.29	W
Thermal Resistance Junction-to-Ambient @ Steady State		$R_{\theta JA}$	420	/ W
Junction and Storage Temperature Range		T_J ,T_{STG}	-55 +150	

ƴ Ordering Information

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3134KADW	F2	34KA	3000	30000	120000	7ñreel

Typical Performance Characteristics

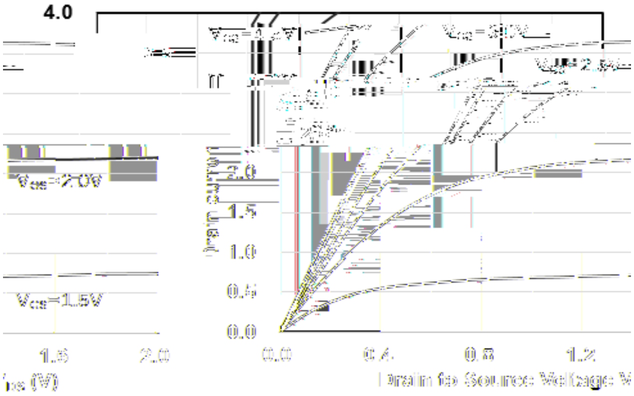


Figure1. Output Characteristics

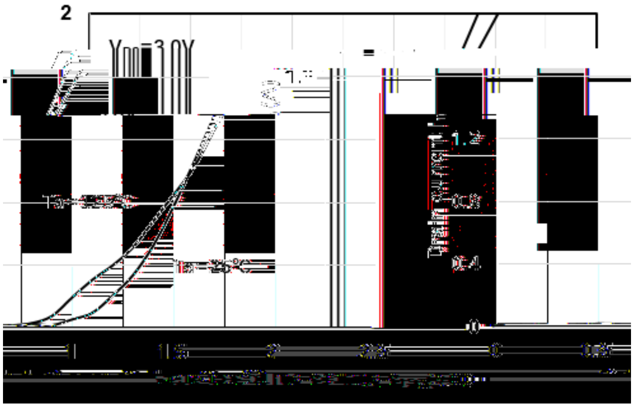


Figure2. Transfer Characteristics

Figure3. Capacitance Characteristics

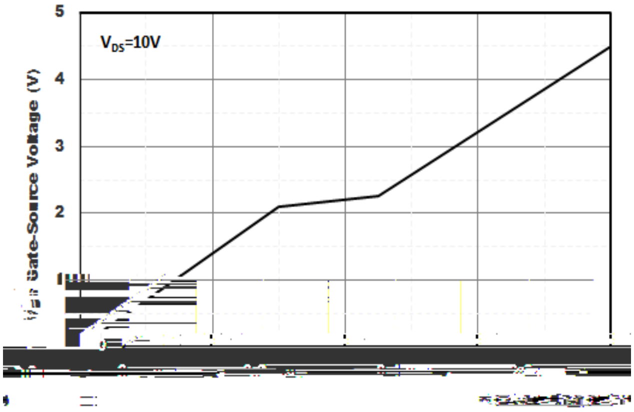


Figure4. Gate Charge

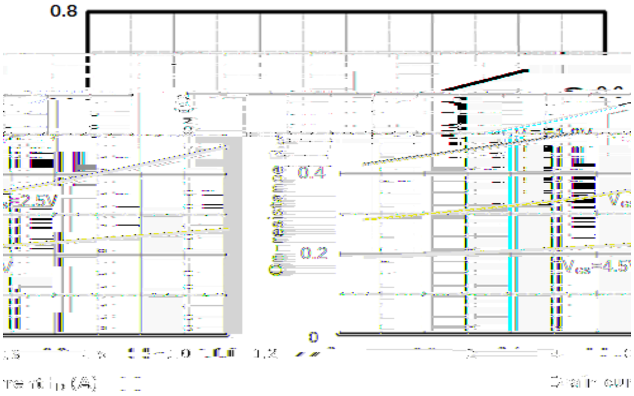


Figure5. Drain-Source on Resistance

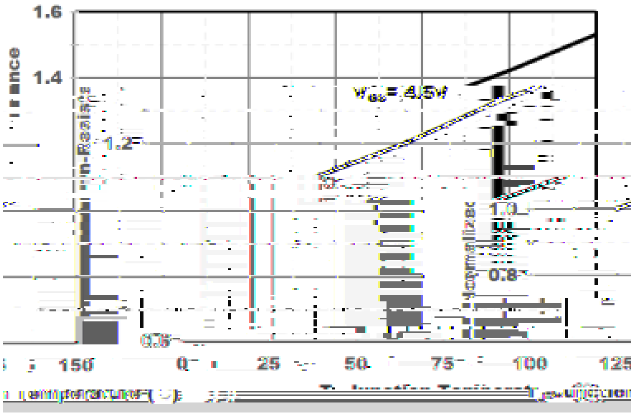


Figure6. Drain-Source on Resistance

L

ýSOT-363 Package information

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the